



Si surfaces - electronic structure and dynamics

Workshop at the Max Born Institute, Berlin-
Adlershof, 9-10th September 2005

Friday 9th

- 13:00 - 14:30 Transport from ECOSS conference location to MBI and **welcome**
- 15:00 Theory of the electronic structure of the Si(001) surface revisited, **Peter Kratzer** (Fritz-Haber-Institute, Berlin, Germany)
- 15:45 Temperature dependence of single electron dynamics at Si(100),
Martin Weinelt (Max-Born-Institute, Berlin, Germany)
- 16:30 **Coffee**
- 17:00 Two-photon photoemission from metallic chains on Si surfaces, **Tilman Rügheimer** (Lehrstuhl für Festkörperphysik, Universität Erlangen, Germany)
- 17:30 Density-dependent carrier dynamics of highly excited Si(111)7x7 dangling bonds, **Ulrich Höfer** (Fachbereich Physik, Universität Marburg, Germany)
- 18:15 Electron dynamics of silicon surface states: Second-harmonic hole burning on Si(111)7x7, **Markus B. Raschke** (Max-Born-Institute, Berlin, Germany)

Saturday 10th

- 9:15 Non-adiabatic molecular dynamics simulations of Si(001) surfaces, **Eckhard Pehlke** (Institut für Theoretische Physik und Astrophysik, Universität Kiel, Germany)
- 10:00 Laser-induced structural instabilities of Si surfaces, **Jun'ichi Kanasaki** (Osaka University, The Institute of Scientific and Industrial Research, Osaka, Japan)
- 10:45 **Coffee**
- 11:15 Electronic structure of Si(100) at high excitation density, **Tanja Gießel** (Max-Born-Institute, Berlin, Germany)
- 11:45 Dynamics of carrier localization and Si-bond rupture on Si surfaces, Katsumi Tanimura (Osaka University, The Institute of Scientific and Industrial Research, Osaka, Japan)
- 12:30 The future of silicon surfaces – concluding remarks, **Thomas Fauster** (Lehrstuhl für Festkörperphysik, Universität Erlangen, Germany)